Abstracts

A true enhancement mode single supply power HFET for portable applications

E. Glass, J.-H. Huang, J. Abrokwah, B. Bernhardt, M. Majerus, E. Spears, R. Droopad and B. Ooms. "A true enhancement mode single supply power HFET for portable applications." 1997 MTT-S International Microwave Symposium Digest 3. (1997 Vol. III [MWSYM]): 1399-1402.

A true enhancement mode heterojunction FET has been developed for low voltage, high efficiency power amplifier applications. A 12 mm wide/spl times/1.0 /spl mu/m gate length device-with no additional circuitry-and only a single voltage supply of 3.5 V exhibited a power output of +31.5 dBm with 75% power-added efficiency at a power gain of 11.6 dB at 850 MHz.

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